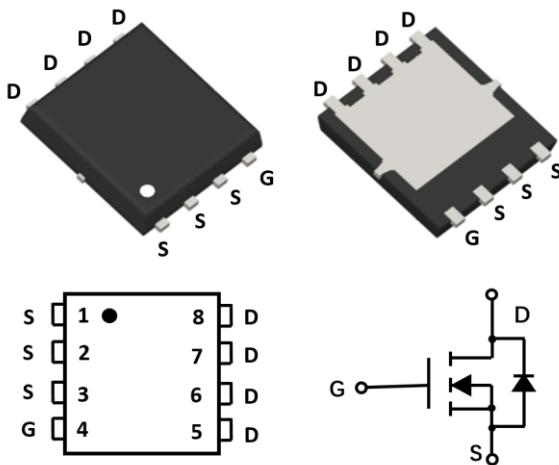




N-Channel Enhancement Mode Field Effect Transistor

PDFN5060-8L



Product Summary

- V_{DS} 80V
- I_D 64A
- I_D (Package limited) 48A
- $R_{DS(on)}$ (at $V_{GS}=10V$) $<8.0\text{ mohm}$
- $R_{DS(on)}$ (at $V_{GS}=4.5V$) $<10.0\text{ mohm}$
- 100% UIS Tested
- 100% ∇V_{DS} Tested

General Description

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery

Applications

- Motor control
- Synchronous-rectification
- Isolated DC/DC convertor
- Invertors

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		V_{DS}	80	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current		I_D	64	A
Drain Current ^A	$T_c=25^\circ\text{C}$	I_D	48	A
	$T_c=100^\circ\text{C}$		30.2	
Pulsed Drain Current ^B		I_{DM}	192	A
Avalanche energy ^C		E_{AS}	25	mJ
Total Power Dissipation ^D	$T_c=25^\circ\text{C}$	P_D	87	W
	$T_c=100^\circ\text{C}$		35	
Thermal Resistance Junction-to-Case		$R_{\theta JC}$	1.72	$^\circ\text{C}/\text{W}$
Thermal Resistance Junction-to-Ambient		$R_{\theta JA}$	62	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range		T_J, T_{STG}	-55~+175	$^\circ\text{C}$

Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJG48G08A	F1	YJG48G08A	5000	10000	50000	13" reel



YJG48G08A

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	80			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}}=80\text{V}, V_{\text{GS}}=0\text{V}$			1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}= 10\text{V}, I_{\text{D}}=12\text{A}$		6.2	8.0	$\text{m}\Omega$
		$V_{\text{GS}}= 4.5\text{V}, I_{\text{D}}=9\text{A}$		7.8	10	
Diode Forward Voltage	V_{SD}	$I_{\text{S}}=20\text{A}, V_{\text{GS}}=0\text{V}$			1.3	V
Maximum Body-Diode Continuous Current	I_{S}				48	A
Gate resistance	R_{G}	f= 1 MHz, Open drain		3.3		Ω
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=100\text{KHZ}$		2028		pF
Output Capacitance	C_{oss}			716		
Reverse Transfer Capacitance	C_{rss}			54		
Switching Parameters						
Total Gate Charge	Q_{g}	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=50\text{V}, I_{\text{D}}=25\text{A}$		28.9		nC
Gate-Source Charge	Q_{gs}			5.4		
Gate-Drain Charge	Q_{gd}			4.9		
Reverse Recovery Chrage	Q_{rr}	$I_{\text{F}}=25\text{A}, di/dt=100\text{A/us}$		61		ns
Reverse Recovery Time	t_{rr}			51		
Turn-on Delay Time	$t_{\text{D(on)}}$			22.5		
Turn-on Rise Time	t_{r}	$V_{\text{GS}}=10\text{V}, V_{\text{DD}}=50\text{V}, I_{\text{D}}=25\text{A}$ $R_{\text{GEN}}=2.5\Omega$		6.3		ns
Turn-off Delay Time	$t_{\text{D(off)}}$			47.5		
Turn-off fall Time	t_{f}			8.8		

- A. The maximum current rating is package limited.
- B. Repetitive rating; pulse width limited by max. junction temperature.
- C. $V_{\text{DD}}=50\text{V}$, $R_{\text{G}}=25\Omega$, $L=0.3\text{mH}$, starting $T_J=25^\circ\text{C}$.
- D. P_d is based on max. junction temperature, using junction-case thermal resistance.



■ Typical Performance Characteristics

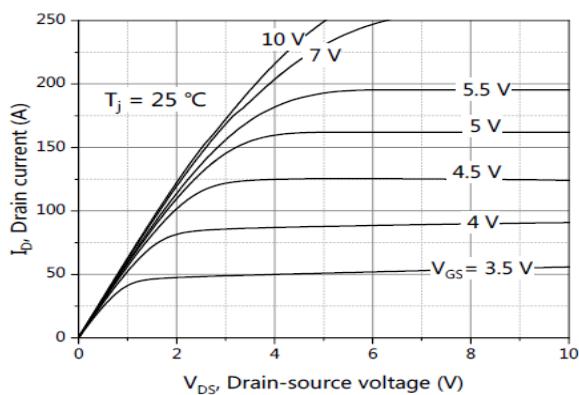


Figure1. Output Characteristics

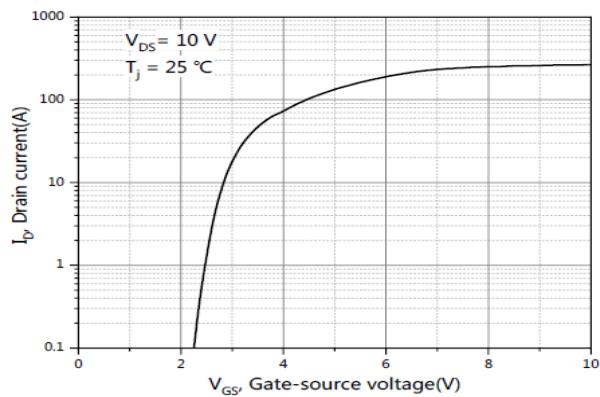


Figure2. Transfer Characteristics

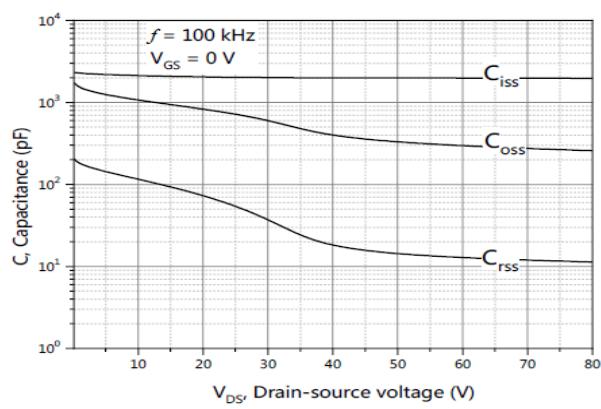


Figure3. Capacitance Characteristics

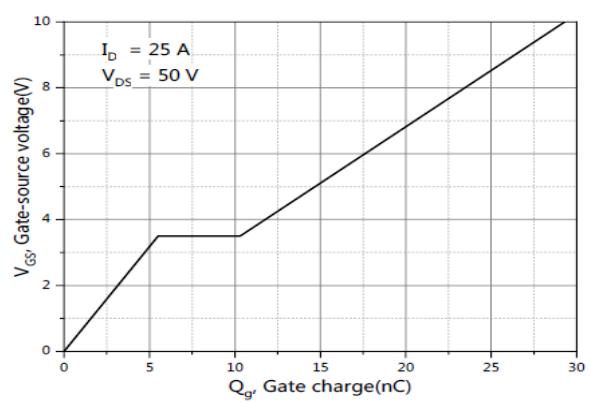


Figure4. Gate Charge

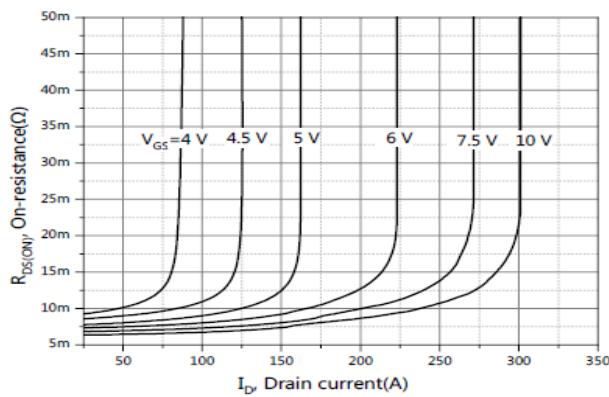


Figure5. Drain-Source on Resistance

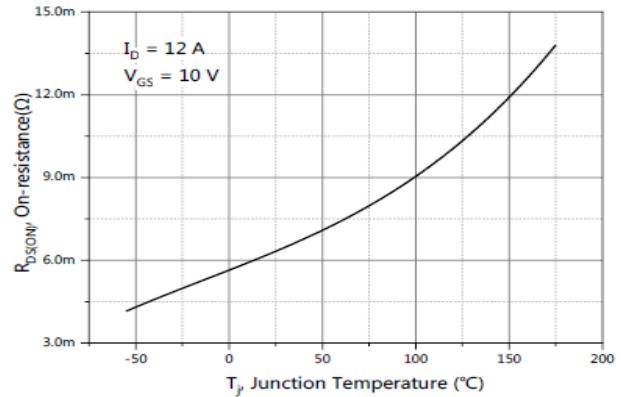


Figure6. Drain-Source on Resistance

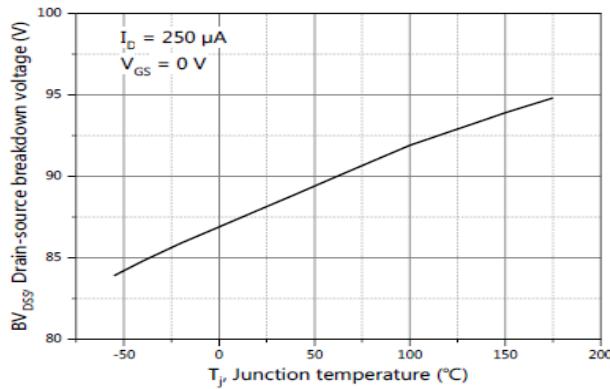


Figure7. Drain-source breakdown voltage

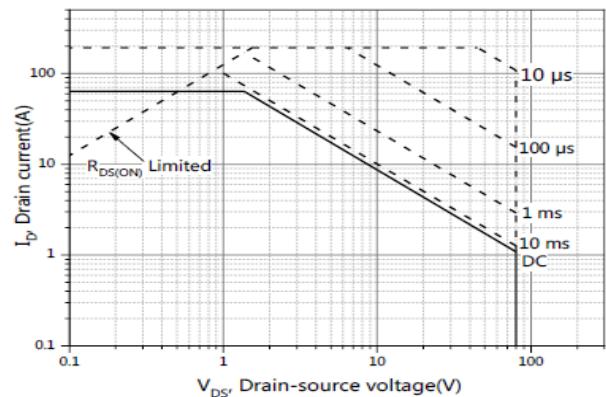


Figure8.Safe Operation Area

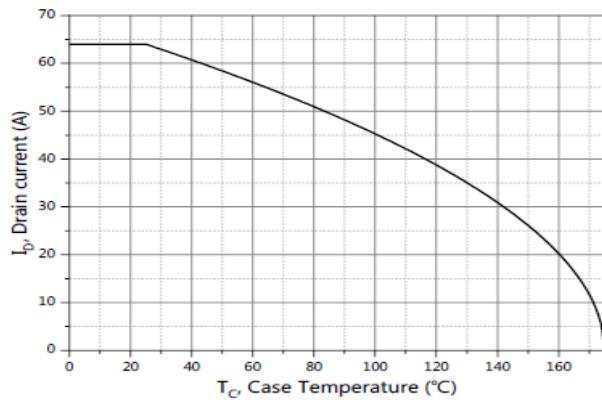


Figure9. Drain current

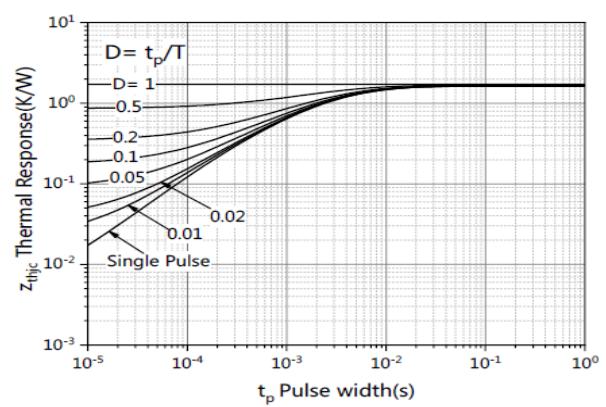
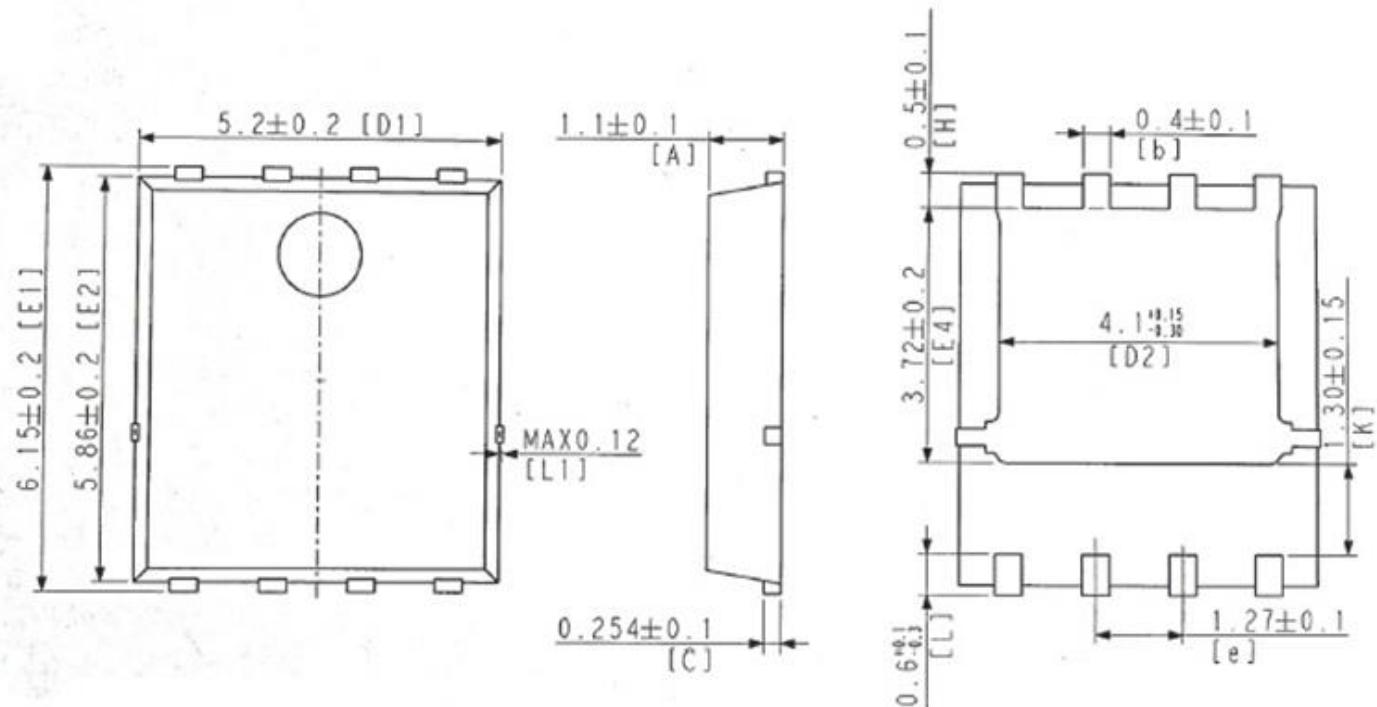


Figure10.Transtent thermal impedance



■ PDFN5060-8L Package information





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